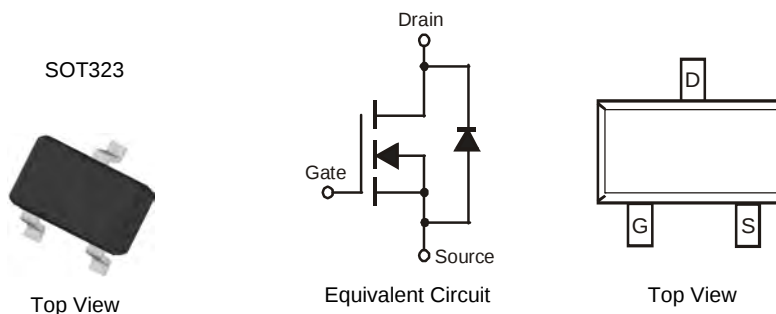


N-CHANNEL ENHANCEMENT MODE MOSFET
Features

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating
- **Lead Free/RoHS Compliant (Note 1)**
- **"Green" Device (Notes 2 & 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

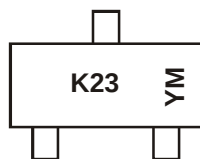
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 3. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)


Ordering Information (Notes 3 & 4)

Part Number	Case	Packaging
BSS123W-7-F	SOT323	3000/Tape & Reel

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information


K23 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: N = 2002)
 M = Month (ex: 9 = September)

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	N	P	R	S	T	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	100	V
Drain-Gate Voltage R _{GS} ≤ 20KΩ	V _{DGR}	100	V
Gate-Source Voltage Continuous	V _{GSS}	±20	V
Drain Current (Note 5) Continuous	I _D	170	mA
Pulsed	I _{DM}	680	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0 10	μA nA	V _{DS} = 100V, V _{GS} = 0V V _{DS} = 20V, V _{GS} = 0V
Gate-Body Leakage, Forward	I _{GSSF}	—	—	50	nA	V _{GS} = 20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	0.8	1.4	2.0	V	V _{DS} = V _{GS} , I _D = 1mA
Static Drain-Source On-Resistance	R _{DS (ON)}	— —	— —	6.0 10	Ω	V _{GS} = 10V, I _D = 0.17A V _{GS} = 4.5V, I _D = 0.17A
Forward Transconductance	g _{FS}	80	370	—	mS	V _{DS} = 10V, I _D = 0.17A, f = 1.0KHz
Drain-Source Diode Forward Voltage	V _{SD}	—	0.84	1.3	V	V _{GS} = 0V, I _S = 0.34A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	29	60	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	10	15	pF	
Reverse Transfer Capacitance	C _{rss}	—	2	6	pF	
SWITCHING CHARACTERISTICS						
Turn-On Rise Time	t _r	—	—	8	ns	V _{DD} = 30V, I _D = 0.28A, R _{GEN} = 50Ω, V _{GS} = 10V
Turn-Off Fall Time	t _f	—	—	16	ns	
Turn-On Delay Time	t _{D(ON)}	—	—	8	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	—	13	ns	

Notes: 5. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at <http://www.diodes.com>.
6. Short duration pulse test used to minimize self-heating effect.

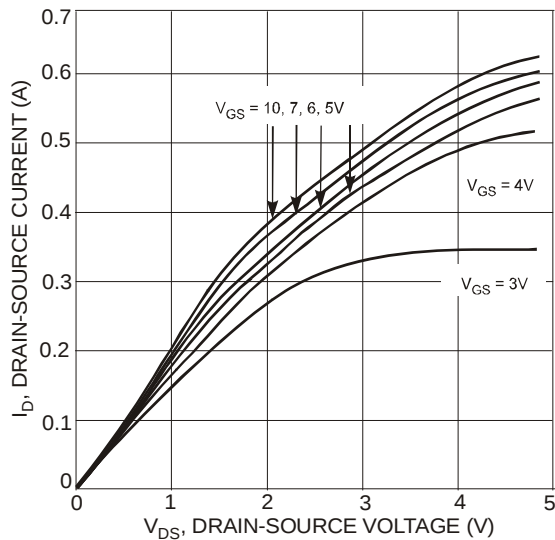


Fig. 1 On-Region Characteristics

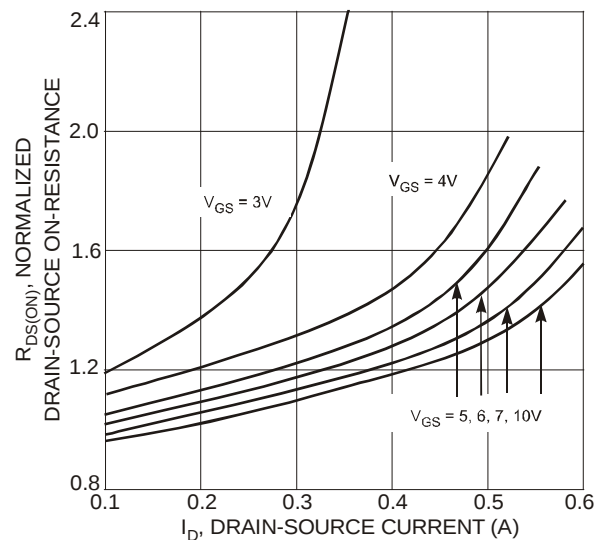


Fig. 2 On-Resistance Variation with Gate Voltage and Drain-Source Current

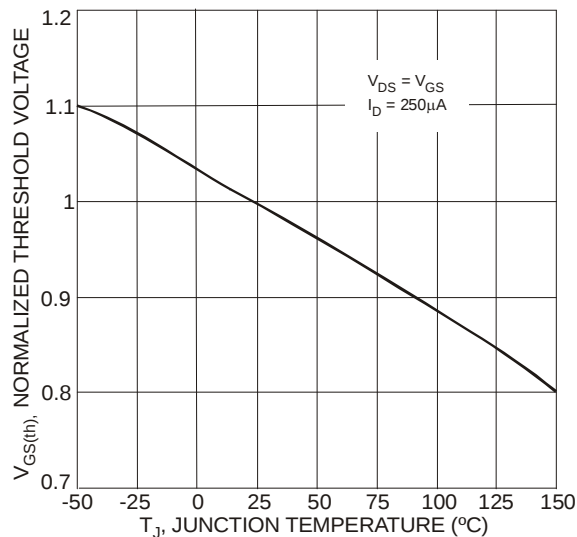


Fig. 3 Gate Threshold Variation with Temperature

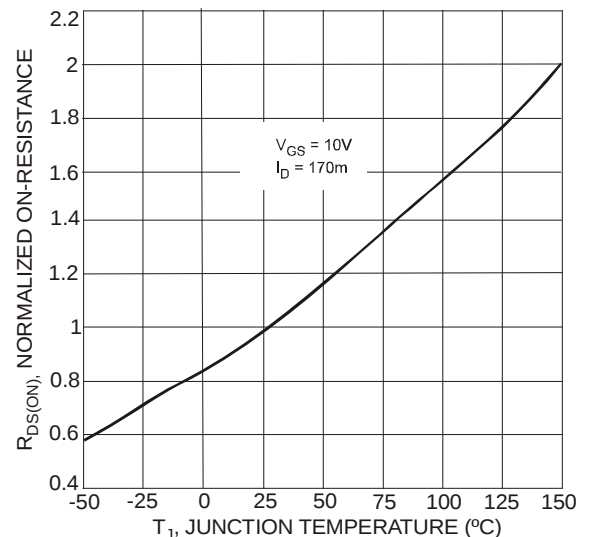


Fig. 4 On-Resistance Variation with Temperature

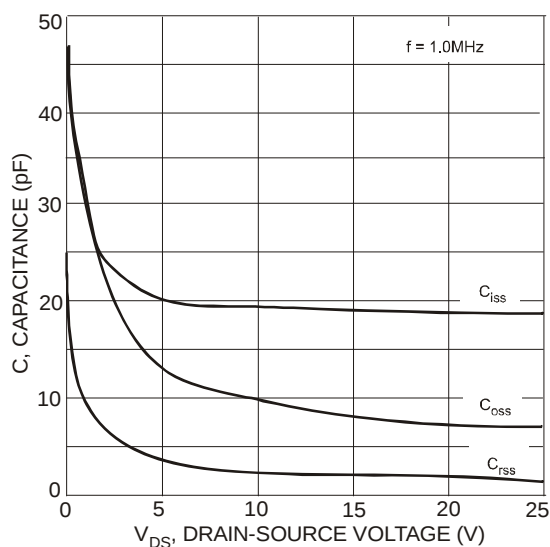


Fig. 5 Typical Capacitance

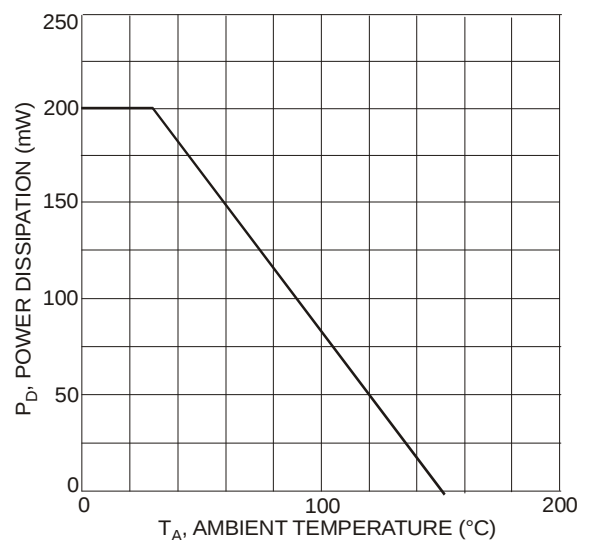
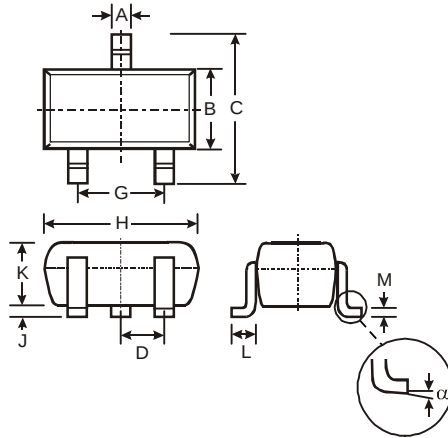


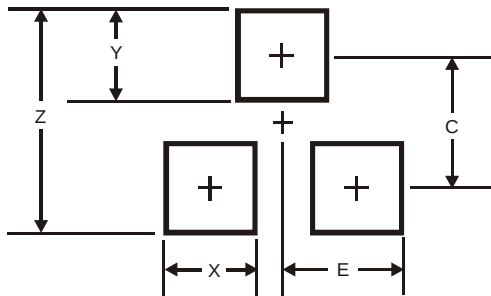
Fig. 6 Power Derating Curve, Total Package

Package Outline Dimensions



SOT323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9